

FEATURES

- Low power:** 1.1 mA/amplifier
- Low wideband noise**
 - 2.1 nV/√Hz input voltage noise
 - 1.4 pA/√Hz input current noise
- Low 1/f noise**
 - 7 nV/√Hz at 10 Hz
 - 13 pA/√Hz at 10 Hz
- Low distortion:** -105 dBc at 100 kHz, $V_o = 2$ V p-p
- High speed**
 - 80 MHz, -3 dB bandwidth ($G = +1$)
 - 12 V/μs slew rate
 - 175 ns settling time to 0.1%
- Low offset voltage:** 0.3 mV maximum
- Rail-to-rail output**
- Wide supply range:** 2.7 V to 12 V
- Known good die (KGD):** these die are fully guaranteed to data sheet specifications

APPLICATIONS

- Low power, low noise signal processing
- Battery-powered instrumentation
- 16-bit PulSAR® ADC drivers

GENERAL DESCRIPTION

The **ADA4841-2KGD** is a unity-gain stable, low noise and distortion, rail-to-rail output amplifier that has a quiescent current of 1.5 mA maximum. Its low power consumption notwithstanding, this amplifier offers low wideband voltage noise performance of 2.1 nV/√Hz and 1.4 pA/√Hz current noise, along with excellent spurious-free dynamic range (SFDR) of -105 dBc at 100 kHz. To maintain a low noise environment at lower frequencies, the amplifier has low 1/f noise of 7 nV/√Hz and 13 pA/√Hz at 10 Hz.

The **ADA4841-2KGD** output can swing to less than 50 mV of either rail. The input common-mode voltage range extends down to the negative supply. The **ADA4841-2KGD** can drive up to 10 pF of capacitive load with minimal peaking.

The **ADA4841-2KGD** provides the performance required to efficiently support emerging 16-bit to 18-bit analog-to-digital converters (ADCs) and is ideal for portable instrumentation, high channel count, industrial measurement, and medical applications. The **ADA4841-2KGD** is ideally suited to drive the **AD7685/AD7686**, 16-bit PulSAR ADCs.

FUNCTIONAL BLOCK DIAGRAM

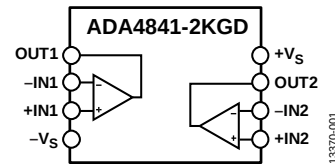


Figure 1.

Additional application and technical information can be found in the **ADA4841-2** data sheet.

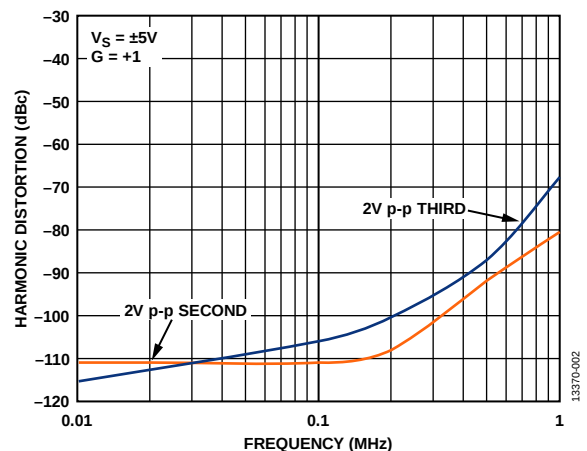


Figure 2. Harmonic Distortion vs. Frequency

TABLE OF CONTENTS

Features	1	Absolute Maximum Ratings	6
Applications.....	1	ESD Caution.....	6
Functional Block Diagram	1	Pin Configuration and Function Descriptions.....	7
General Description	1	Outline Dimensions	8
Revision History	2	Die Specifications and Assembly Recommendations	8
Specifications.....	3	Ordering Guide.....	9
±5 V Supply	3		
5 V Supply.....	4		
3 V Supply.....	5		

REVISION HISTORY

5/2017—Rev. 0 to Rev. A	
Added CP-8-10	Throughout
Updated Outline Dimensions	8
Changes to Ordering Guide	9

9/2015—Revision 0: Initial Version

SPECIFICATIONS

±5 V SUPPLY

$T_A = 25^\circ\text{C}$, $R_L = 1\text{ k}\Omega$, $G = +1$, unless otherwise noted.

Table 1.

Parameter	Test Conditions/Comments	Min	Typ	Max	Unit
DYNAMIC PERFORMANCE					
–3 dB Bandwidth	$V_O = 0.02\text{ V p-p}$		80		MHz
	$V_O = 2\text{ V p-p}$		3		MHz
Slew Rate	$G = +1$, $V_O = 9\text{ V step}$, $R_L = 1\text{ k}\Omega$		13		V/ μs
Settling Time to 0.1%	$G = +1$, $V_O = 8\text{ V step}$		650		ns
Settling Time to 0.01%	$G = +1$, $V_O = 8\text{ V step}$		1000		ns
NOISE/HARMONIC PERFORMANCE					
Harmonic Distortion, HD2/HD3	$f_C = 100\text{ kHz}$, $V_O = 2\text{ V p-p}$, $G = +1$		–111/–105		dBc
	$f_C = 1\text{ MHz}$, $V_O = 2\text{ V p-p}$		–80/–67		dBc
Input Voltage Noise	$f = 100\text{ kHz}$		2.1		nV/ $\sqrt{\text{Hz}}$
Input Current Noise	$f = 100\text{ kHz}$		1.4		pA/ $\sqrt{\text{Hz}}$
DC PERFORMANCE					
Input Offset Voltage			40	300	μV
Input Offset Voltage Drift			1		$\mu\text{V}/^\circ\text{C}$
Input Bias Current			3	5.3	μA
Input Offset Current			0.1	0.5	μA
Open-Loop Gain	$V_O = \pm 4\text{ V}$	103	120		dB
INPUT CHARACTERISTICS					
Input Resistance					
Common Mode			90		M Ω
Differential Mode			25		k Ω
Input Capacitance					
Common Mode			1		pF
Differential Mode			3		pF
Input Common-Mode Voltage Range		–5.1		+4	V
Common-Mode Rejection Ratio (CMRR)	$V_{CM} = \Delta 4\text{ V}$	95	115		dB
MATCHING CHARACTERISTICS					
Input Offset Voltage			70		μV
Input Bias Current			60		nA
OUTPUT CHARACTERISTICS					
Output Voltage Swing	$G > +1$	± 4.9	± 4.955		V
Output Current Limit	Sourcing, $V_{IN} = +V_S$, $R_L = 50\text{ }\Omega$ to GND		30		mA
	Sinking, $V_{IN} = -V_S$, $R_L = 50\text{ }\Omega$ to GND		60		mA
Capacitive Load Drive	30% overshoot		15		pF
POWER SUPPLY					
Operating Range		2.7		12	V
Quiescent Current per Amplifier			1.2	1.5	mA
Positive Power Supply Rejection Ratio	$+V_S = +5\text{ V to }+6\text{ V}$, $-V_S = -5\text{ V}$	95	110		dB
Negative Power Supply Rejection Ratio	$+V_S = +5\text{ V}$, $-V_S = -5\text{ V to }-6\text{ V}$	96	120		dB

5 V SUPPLY

$T_A = 25^\circ\text{C}$, $R_L = 1\text{ k}\Omega$, $G = +1$, $V_{CM} = 2.5\text{ V}$, unless otherwise noted.

Table 2.

Parameter	Test Conditions/Comments	Min	Typ	Max	Unit
DYNAMIC PERFORMANCE					
–3 dB Bandwidth	$V_O = 0.02\text{ V p-p}$		80		MHz
	$V_O = 2\text{ V p-p}$		3		MHz
Slew Rate	$G = +1$, $V_O = 4\text{ V step}$, $R_L = 1\text{ k}\Omega$		12		V/ μs
Settling Time to 0.1%	$G = +1$, $V_O = 2\text{ V step}$		175		ns
Settling Time to 0.01%	$G = +1$, $V_O = 2\text{ V step}$		550		ns
NOISE/HARMONIC PERFORMANCE					
Harmonic Distortion, HD2/HD3	$f_C = 100\text{ kHz}$, $V_O = 2\text{ V p-p}$		–109/–105		dBc
	$f_C = 1\text{ MHz}$, $V_O = 2\text{ V p-p}$		–78/–66		dBc
Input Voltage Noise	$f = 100\text{ kHz}$		2.1		nV/ $\sqrt{\text{Hz}}$
Input Current Noise	$f = 100\text{ kHz}$		1.4		pA/ $\sqrt{\text{Hz}}$
Crosstalk	$f = 100\text{ kHz}$		–117		dB
DC PERFORMANCE					
Input Offset Voltage			40	300	μV
Input Offset Voltage Drift			1		$\mu\text{V}/^\circ\text{C}$
Input Bias Current			3	5.3	μA
Input Offset Current			0.1	0.4	μA
Open-Loop Gain	$V_O = 0.5\text{ V to }4.5\text{ V}$	103	124		dB
INPUT CHARACTERISTICS					
Input Resistance					
Common Mode			90		M Ω
Differential Mode			25		k Ω
Input Capacitance					
Common Mode			1		pF
Differential Mode			3		pF
Input Common-Mode Voltage Range		–0.1		+4	V
Common-Mode Rejection Ratio (CMRR)	$V_{CM} = \Delta 1.5\text{ V}$	88	115		dB
MATCHING CHARACTERISTICS					
Input Offset Voltage			70		μV
Input Bias Current			70		nA
OUTPUT CHARACTERISTICS					
Output Voltage Swing	$G > +1$	0.08 to 4.92	0.029 to 4.974		V
Output Current Limit	Sourcing, $V_{IN} = +V_S$, $R_L = 50\text{ }\Omega$ to V_{CM}		30		mA
	Sinking, $V_{IN} = -V_S$, $R_L = 50\text{ }\Omega$ to V_{CM}		60		mA
Capacitive Load Drive	30% overshoot		15		pF
POWER SUPPLY					
Operating Range		2.7		12	V
Quiescent Current per Amplifier			1.1	1.4	mA
Positive Power Supply Rejection Ratio	$+V_S = +5\text{ V to }+6\text{ V}$, $-V_S = 0\text{ V}$	95	110		dB
Negative Power Supply Rejection Ratio	$+V_S = +5\text{ V}$, $-V_S = 0\text{ V to }-1\text{ V}$	96	120		dB

3 V SUPPLY

$T_A = 25^\circ\text{C}$, $R_L = 1\text{ k}\Omega$, $G = +1$, $V_{CM} = 1.5\text{ V}$, unless otherwise noted.

Table 3.

Parameter	Test Conditions/Comments	Min	Typ	Max	Unit
DYNAMIC PERFORMANCE					
–3 dB Bandwidth	$V_O = 0.02\text{ V p-p}$		80		MHz
Slew Rate	$G = +1$, $V_O = 2\text{ V step}$, $R_L = 1\text{ k}\Omega$		12		V/ μs
Settling Time to 0.1%	$G = +1$, $V_O = 1\text{ V step}$		120		ns
Settling Time to 0.01%	$G = +1$, $V_O = 1\text{ V step}$		250		ns
NOISE/HARMONIC PERFORMANCE					
Harmonic Distortion, HD2/HD3	$f_c = 100\text{ kHz}$, $V_O = 1\text{ V p-p}$		–97/–100		dBc
	$f_c = 1\text{ MHz}$, $V_O = 1\text{ V p-p}$		–79/–80		dBc
Input Voltage Noise	$f = 100\text{ kHz}$		2.1		nV/ $\sqrt{\text{Hz}}$
Input Current Noise	$f = 100\text{ kHz}$		1.4		pA/ $\sqrt{\text{Hz}}$
DC PERFORMANCE					
Input Offset Voltage	$V_O = 0.5\text{ V to }2.5\text{ V}$		40	300	μV
Input Offset Voltage Drift			1		$\mu\text{V}/^\circ\text{C}$
Input Bias Current			3	5.3	μA
Input Offset Current			0.1	0.5	μA
Open-Loop Gain		101	123		dB
INPUT CHARACTERISTICS					
Input Resistance	$V_{CM} = \Delta 0.4\text{ V}$				
Common Mode			90		M Ω
Differential Mode			25		k Ω
Input Capacitance					
Common Mode			1		pF
Differential Mode			3		pF
Input Common-Mode Voltage Range		–0.1		+2	V
Common-Mode Rejection Ratio (CMRR)		86	115		dB
MATCHING CHARACTERISTICS					
Input Offset Voltage			70		μV
Input Bias Current			60		nA
OUTPUT CHARACTERISTICS					
Output Voltage Swing	$G > +1$	0.045 to 2.955	0.023 to 2.988		V
Output Current Limit	Sourcing, $V_{IN} = +V_S$, $R_L = 50\text{ }\Omega$ to V_{CM}		30		mA
	Sinking, $V_{IN} = -V_S$, $R_L = 50\text{ }\Omega$ to V_{CM}		60		mA
Capacitive Load Drive	30% overshoot		30		pF
POWER SUPPLY					
Operating Range		2.7		12	V
Quiescent Current per Amplifier			1.1	1.3	mA
Positive Power Supply Rejection Ratio	$+V_S = +3\text{ V to }+4\text{ V}$, $-V_S = 0\text{ V}$	95	110		dB
Negative Power Supply Rejection Ratio	$+V_S = +3\text{ V}$, $-V_S = 0\text{ V to }-1\text{ V}$	96	120		dB

ABSOLUTE MAXIMUM RATINGS

Table 4.

Parameter	Rating
Supply Voltage	12.6 V
Common-Mode Input Voltage	$-V_s - 0.5\text{ V}$ to $+V_s + 0.5\text{ V}$
Differential Input Voltage	$\pm 1.8\text{ V}$
Storage Temperature Range	-65°C to $+125^{\circ}\text{C}$
Junction Temperature	150°C

Stresses at or above those listed under Absolute Maximum Ratings may cause permanent damage to the product. This is a stress rating only; functional operation of the product at these or any other conditions above those indicated in the operational section of this specification is not implied. Operation beyond the maximum operating conditions for extended periods may affect product reliability.

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

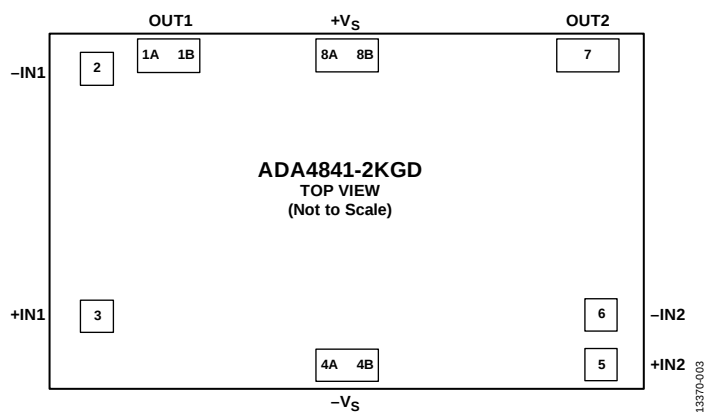


Figure 3. Pin Configuration

Table 5. Pin Function Descriptions

Pin No.	Mnemonic	X-Axis	Y-Axis	Description
1A, 1B	OUT1	-463, -393	+363	Output 1, Double Bond Pad
2	-IN1	-597	+334	Inverting Input 1
3	+IN1	-597	-250	Noninverting Input 1
4A, 4B	-Vs	-36, +35	-363	Negative Supply, Double Bond Pad
5	+IN2	+603	-363	Noninverting Input 2
6	-IN2	+603	-245	Inverting Input 2
7	OUT2	+568	+363	Output 2
8A, 8B	+Vs	-36, +35	+363	Positive Supply, Double Bond Pad

OUTLINE DIMENSIONS



Figure 4. 8-Pad Bare Die [CHIP]
(C-8-4)
Dimensions shown in millimeters

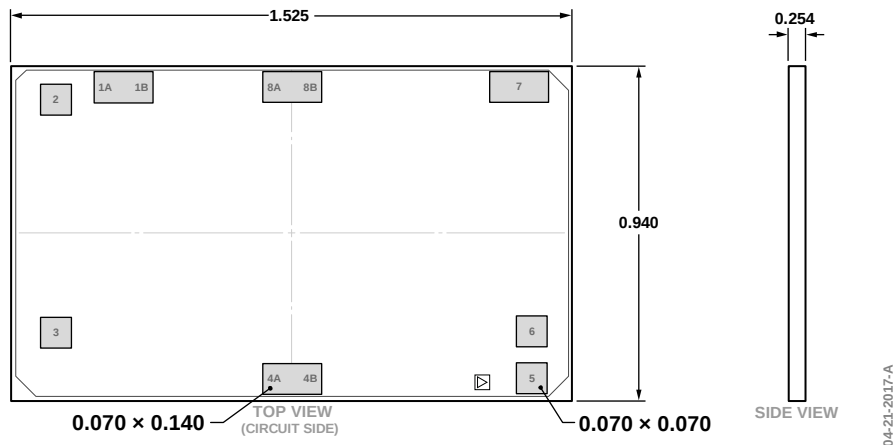


Figure 5. 8-Pad Bare Die [CHIP]
(C-8-10)
Dimensions shown in millimeters

DIE SPECIFICATIONS AND ASSEMBLY RECOMMENDATIONS

Table 6. Die Specifications

Parameter	Value	Unit
Scribe Line Width	75	µm
Die Size (Maximum Size)	1525 × 940	µm
Thickness		
ADA4841-2KGD-WP	305	µm
ADA4841-2KGD-PT	254	µm
Bond Pads (Minimum Size)	70 × 70	µm
Bond Pad Composition	0.5% AlCu	%
Backside	Silicon on insulator (SOI)	Not applicable
Passivation	Doped-oxide/SiN	Not applicable
ESD, Human Body Model (HBM)	2000	V

Table 7. Assembly Recommendations

Assembly Component	Recommendation
Die Attach	Ablestik 84-1LMISR4
Bonding Method	1 mil gold

ORDERING GUIDE

Model	Temperature Range	Package Description	Package Option
ADA4841-2KGD-WP	–40°C to +125°C	8-Pad Bare Die [CHIP], Waffle Package	C-8-4
ADA4841-2KGD-PT	–40°C to +125°C	8-Pad Bare Die [CHIP], Pocket Tape	C-8-10

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